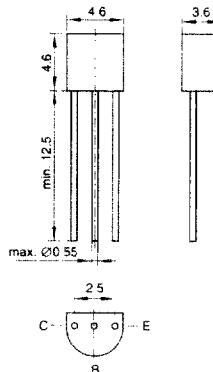


PNP Silicon Epitaxial Planar Transistors

for switching and amplifier applications. Especially suitable for AF-driver stages and low-power output stages.

These types are also available subdivided into three groups -16, -25, and -40, according to their DC current gain. As complementary types, the NPN transistors BC337 and BC338 are recommended.

On special request, these transistors are also manufactured in the pin configuration TO-18.

**TO-92 Plastic Package**

Weight approx. 0.18 g

Dimensions in mm

Absolute Maximum Ratings

	Symbol	Value	Unit
Collector-Emitter Voltage BC327 BC328	$-V_{CES}$	50	V
	$-V_{CES}$	30	V
Collector-Emitter Voltage BC327 BC328	$-V_{CEO}$	45	V
	$-V_{CEO}$	25	V
Emitter-Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	800	mA
Peak Collector Current	$-I_{CM}$	1	A
Base Current	$-I_B$	100	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	625 ¹⁾	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_S	-65...+150	$^\circ\text{C}$

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

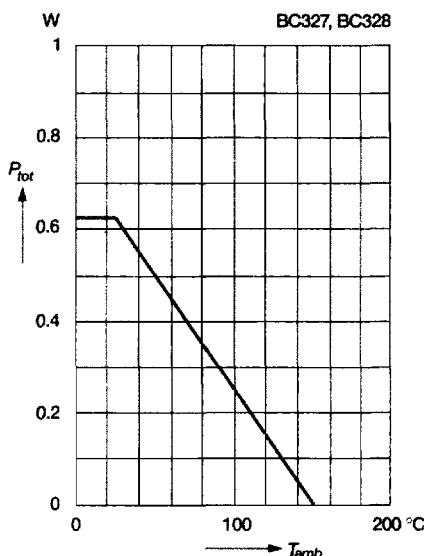
Characteristics at $T_{amb} = 25^\circ C$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 1 V$, $-I_C = 100 mA$					
Current Gain Group-16					
-25	h_{FE}	100	160	250	-
-40	h_{FE}	160	250	400	-
-40	h_{FE}	250	400	630	-
at $-V_{CE} = 1 V$, $-I_C = 300 mA$					
Current Gain Group-16					
-25	h_{FE}	60	130	-	-
-40	h_{FE}	100	200	-	-
-40	h_{FE}	170	320	-	-
Thermal Resistance Junction to Ambient Air	R_{thA}	-	-	200 ¹⁾	K/W
Collector-Emitter Cutoff Current at $-V_{CE} = 45 V$	BC327	$-I_{CES}$	-	2	100
at $-V_{CE} = 25 V$	BC328	$-I_{CES}$	-	2	100
at $-V_{CE} = 45 V$, $T_{amb} = 125^\circ C$	BC327	$-I_{CES}$	-	10	nA
at $-V_{CE} = 25 V$, $T_{amb} = 125^\circ C$	BC328	$-I_{CES}$	-	10	μA
Collector-Emitter Breakdown Voltage at $-I_C = 10 mA$	BC327 BC328	$-V_{(BR)CEO}$ $-V_{(BR)CEO}$	45 25	-	-
Collector-Emitter Breakdown Voltage at $-I_C = 0.1 mA$	BC327 BC328	$-V_{(BR)CES}$ $-V_{(BR)CES}$	50 30	-	-
Emitter-Base Breakdown Voltage at $-I_E = 0.1 mA$		$-V_{(BR)EBO}$	5	-	-
Collector Saturation Voltage at $-I_C = 500 mA$, $-I_B = 50 mA$		$-V_{CEsat}$	-	-	0.7
Base-Emitter Voltage at $-V_{CE} = 1 V$, $-I_C = 300 mA$		$-V_{BE}$	-	-	1.2
Gain-Bandwidth Product at $-V_{CE} = 5 V$, $-I_C = 10 mA$, $f = 50 MHz$		f_T	-	100	-
Collector-Base Capacitance at $-V_{CB} = 10 V$, $f = 1 MHz$		C_{CBO}	-	12	-
1) Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.					

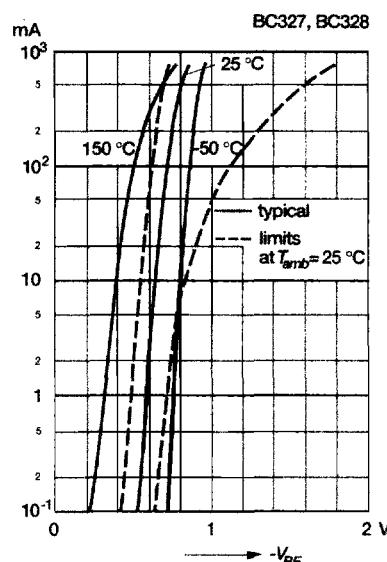
BC327, BC328

Admissible power dissipation versus ambient temperature

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

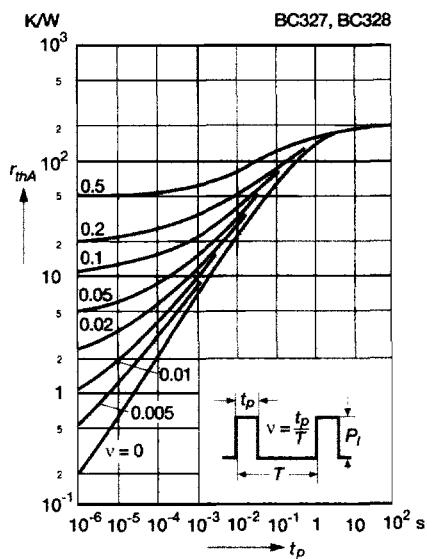


Collector current versus base-emitter voltage

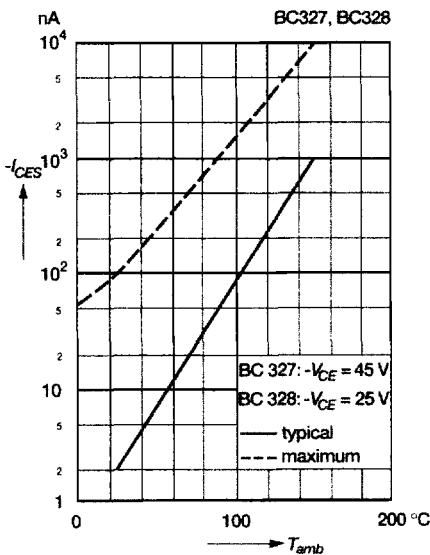


Pulse thermal resistance versus pulse duration

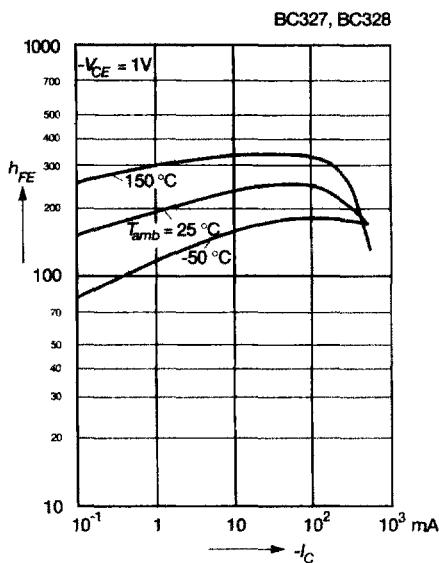
Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



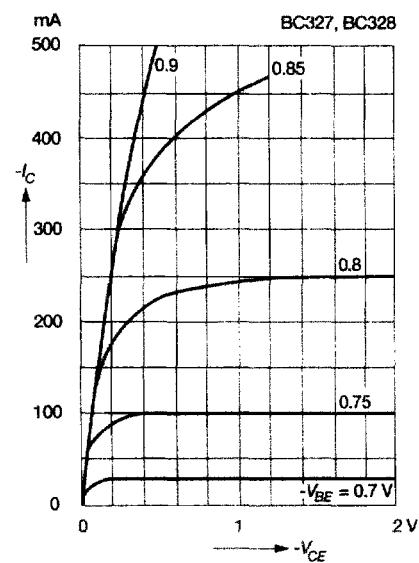
Collector-emitter cutoff current versus ambient temperature



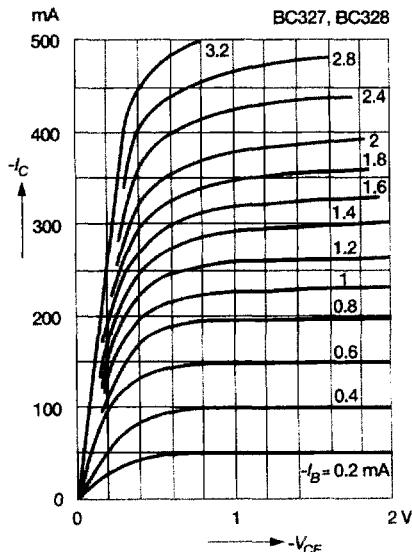
**DC current gain
versus collector current**



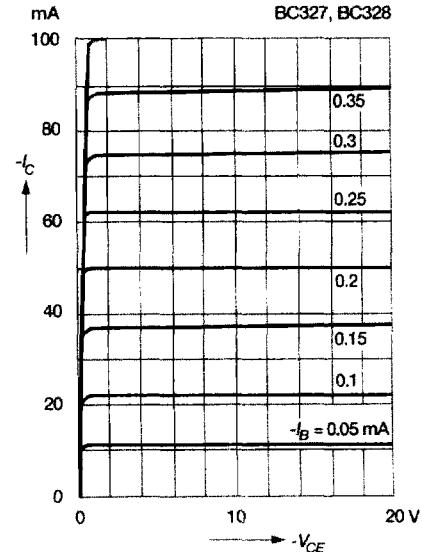
**Common emitter
collector characteristics**



**Common emitter
collector characteristics**

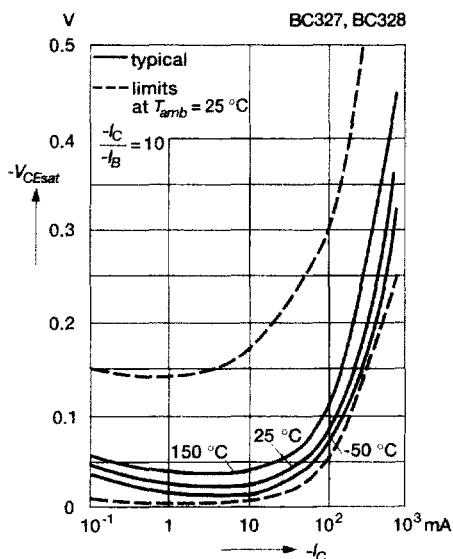


**Common emitter
collector characteristics**

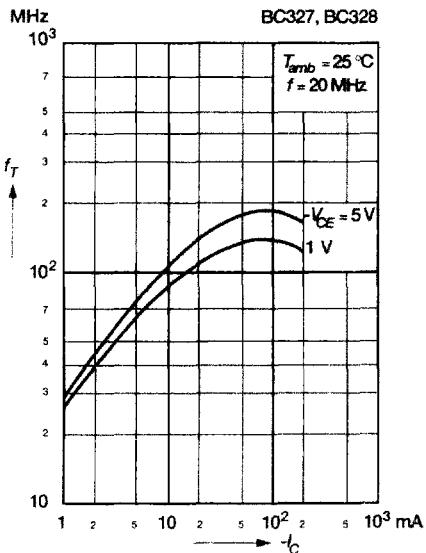


BC327, BC328

Collector saturation voltage
versus collector current



Gain-bandwidth product
versus collector current



Base saturation voltage
versus collector current

